



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

2SC2551 TRANSISTOR (NPN)

FEATURES

- High voltage
- Low saturation voltage
- Small collector output capacitance
- Complementary to 2SA1091

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

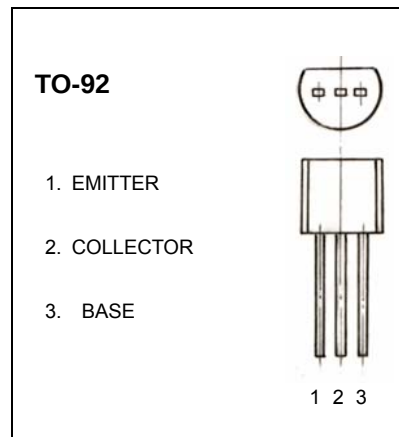
Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	100	mA
P_C	Collector power dissipation	400	mW
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}$, $I_E=0$	300			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}$, $I_B=0$	300			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}$, $I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=300\text{V}$, $I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6\text{V}$, $I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=10\text{V}$, $I_C=20\text{mA}$	30		150	
	$h_{FE(2)}$	$V_{CE}=10\text{V}$, $I_C=1\text{mA}$	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=20\text{mA}$, $I_B=2\text{mA}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=20\text{mA}$, $I_B=2\text{mA}$			1.2	V
Transition frequency	f_T	$V_{CE}=10\text{V}$, $I_C=20\text{mA}$		80		MHz
Collector output capacitance	C_{ob}	$V_{CB}=20\text{V}$, $I_E=0$, $f=1\text{MHz}$			4	pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	O
Range	30-90	50-150



Typical Characteristics

2SC2551

